

[illegible]

FIG. 3A

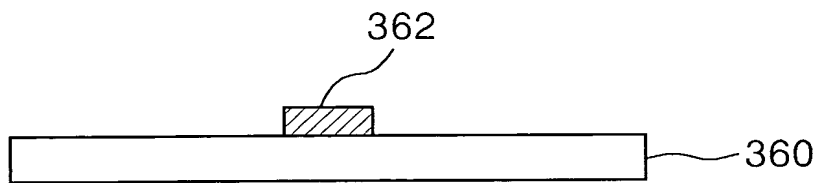


FIG. 3B

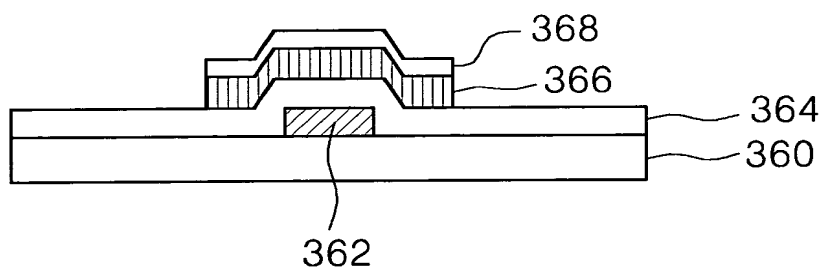
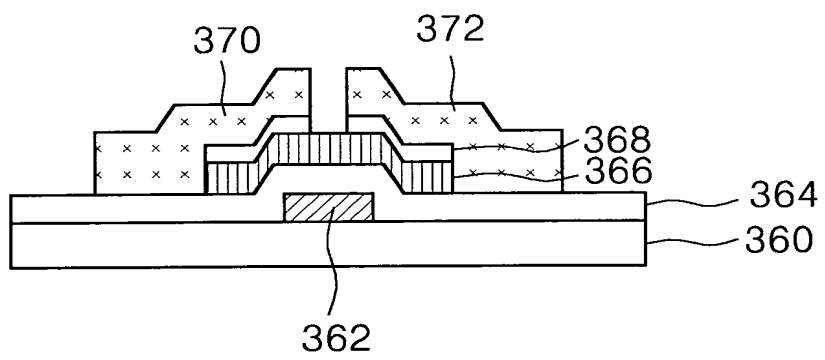


FIG. 3C



This cross-sectional view shows a substrate 360 with a thin layer 362 on its top surface. A patterned layer 368 is formed on top of layer 362. The layer 368 has a complex profile with several rectangular features. The top surface of the layer 368 is labeled 370. The side walls of the features are labeled 372 and 376. The bottom surface of the layer 368 is labeled 366. The layer 368 is filled with a material indicated by 'x' marks.

A cross-sectional view of a semiconductor device. The device consists of a substrate 360 with a central opening 362. A layer 364 is formed on the substrate, with a central portion 366 and side portions 368. A layer 370 is formed on top of the side portions 368, with a central portion 372 and side portions 379. A layer 376 is formed on top of the side portions 379, with a central portion 372 and side portions 379. A layer 376 is also formed on the side portions 379, with a central portion 372 and side portions 379.

FIG. 4A

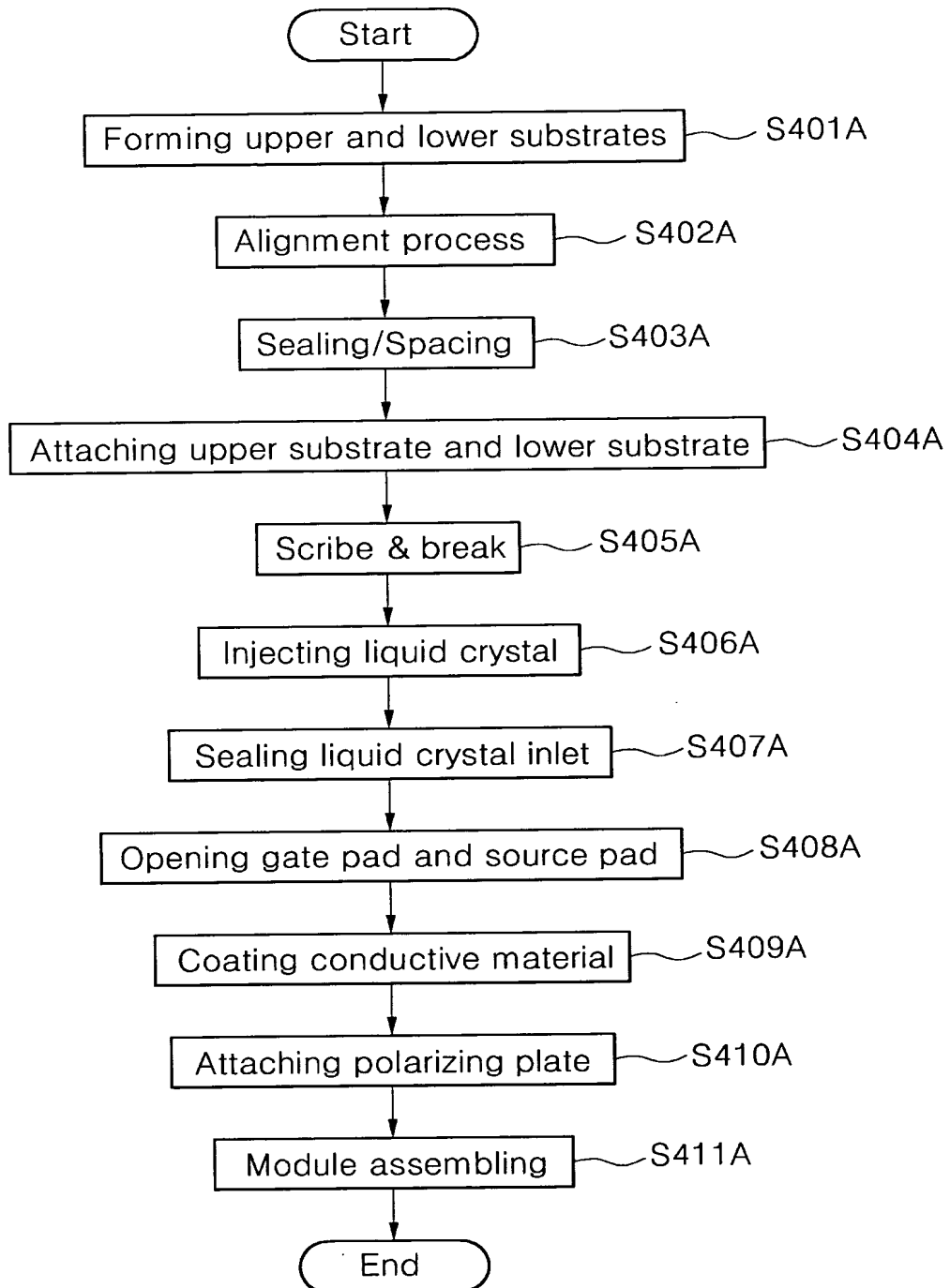


FIG. 4B

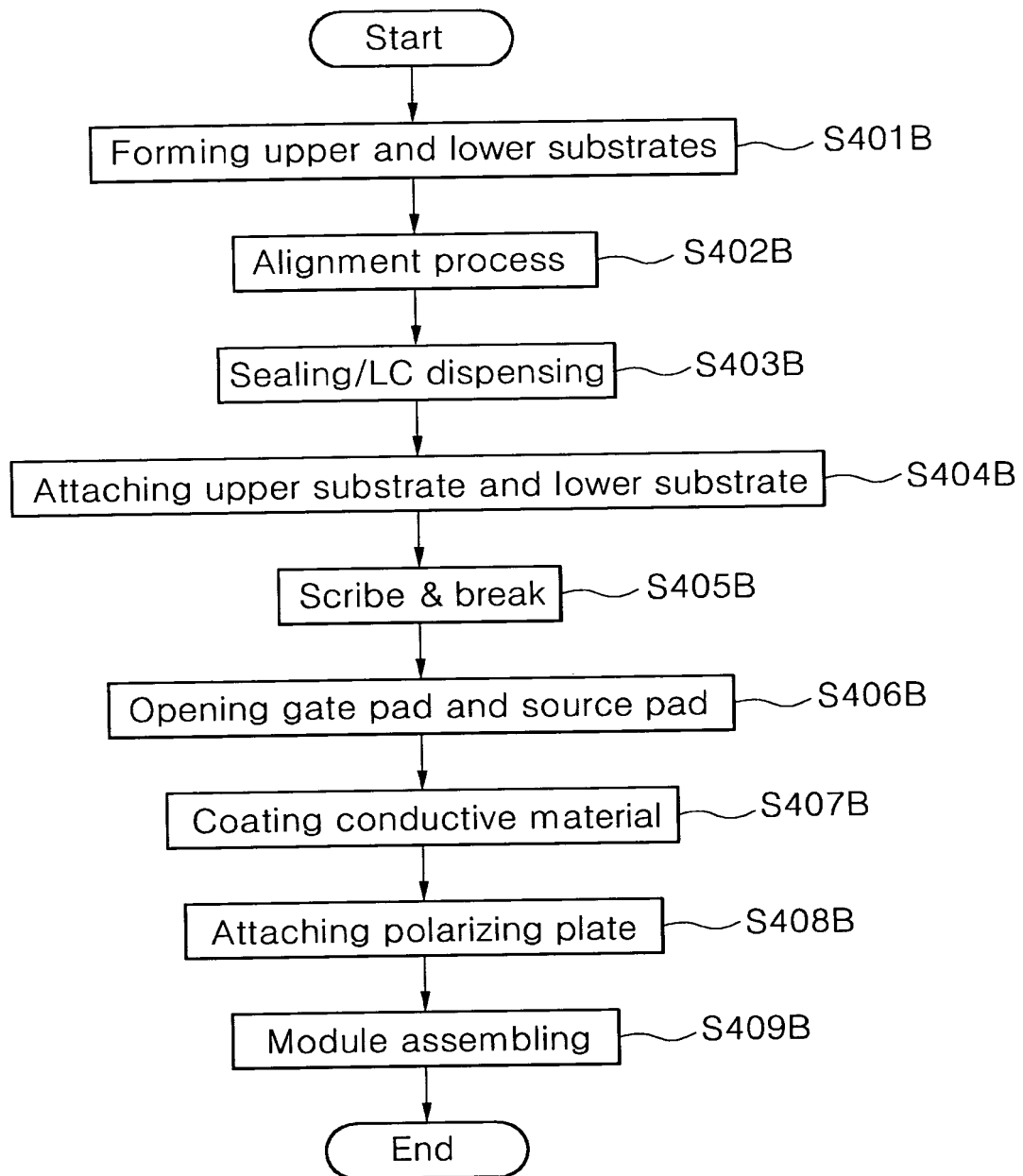


FIG. 5

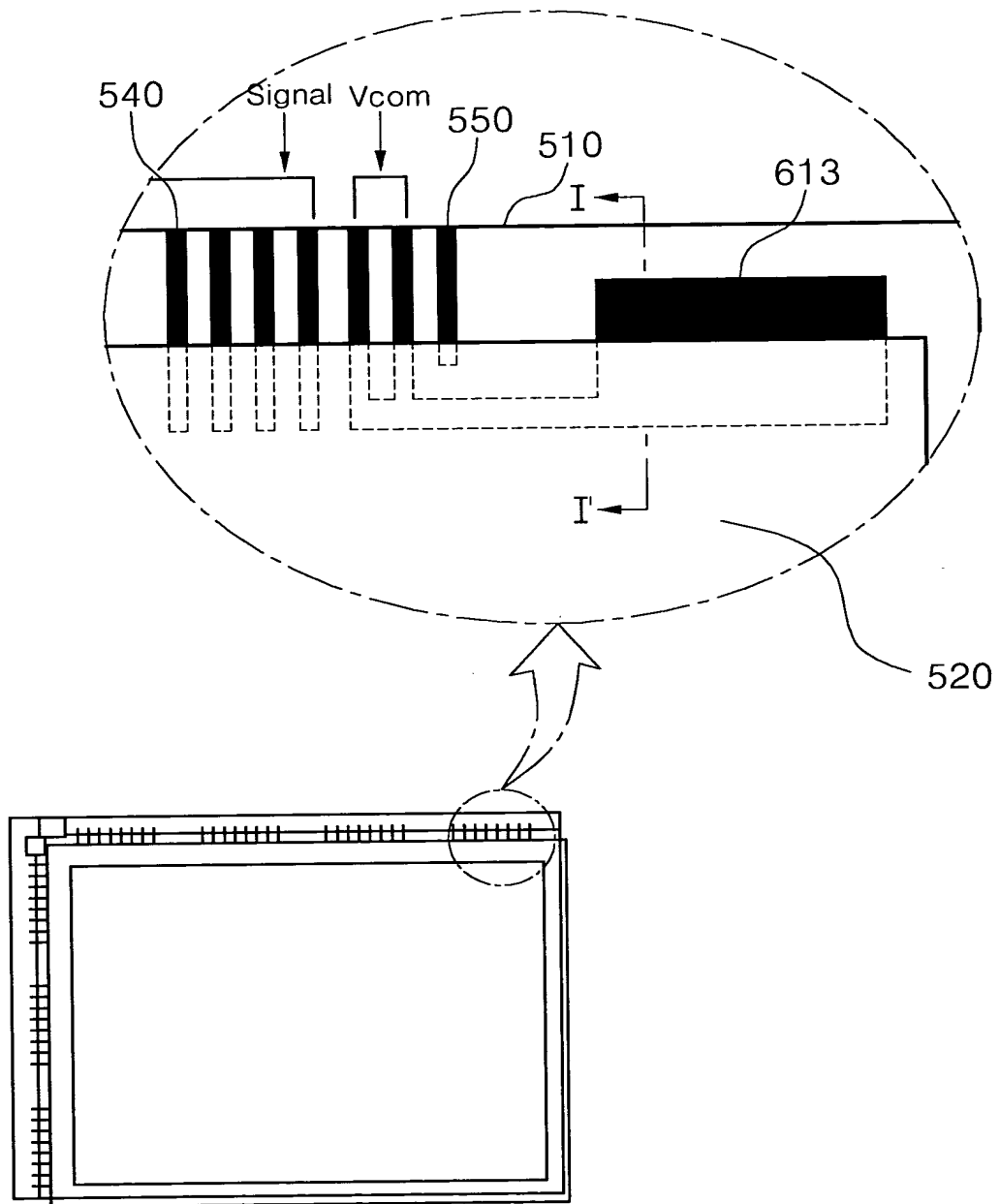


FIG. 6

